

Chip Specification

General Description:

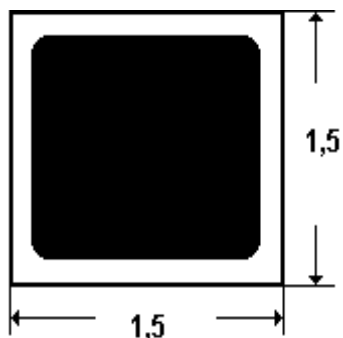
Schottky Diode chips with Mo-barrier for switch mode power rectifiers with the following features:

- * **Guard-ring for stress protection**
- * **Extremely low forward voltage**
- * **125 °C operation junction temperature**
- * **reverse avalanche behavior**

Mechanical Data:

SB 3XX passivated Silicon Chip

Demension(mm)	1,5x1,5
Thickness:	350 +- 20 μm
Metallization:	
Top (Anode) :	Al Ag
Bottom (Cathode) :	TiNiAg



Forward Current(A)	3 A
Reverse Voltage (V):	23, 43, 100 V

Type	Chip	V _R (V)	V _F (V)@25 C	I _{RM} @V _{RMM}
	size(mm)		at I _f =1A	at 25 C
SB320	1,5x1,5	23 V	440mV	0,5mA
SB340	1,5x1,5	43 V	510mV	0,5mA
SB2100	1,5x1,5	100 V	730mV	0,5mA

Note: Other voltages, V_f & Top Metal AL are available

